

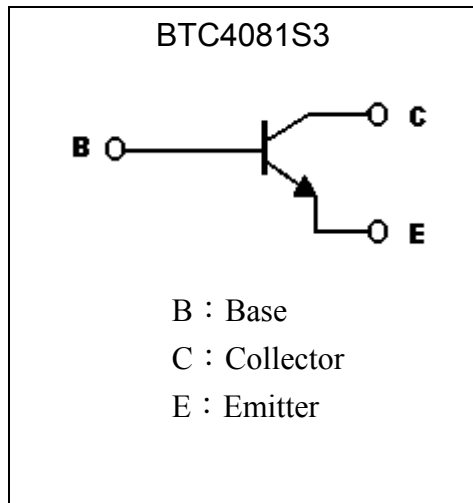
**General Purpose NPN Epitaxial Planar Transistor**

# BTC4081S3

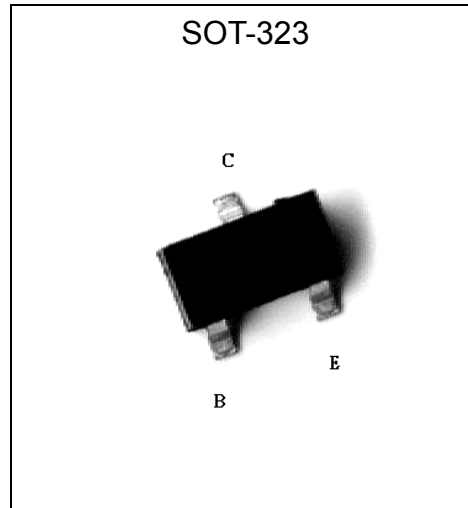
## Description

- The BTC4081S3 is designed for using in driver stage of AF amplifier and general purpose amplification.
- Low Cob, Typ. Cob=2.0pF
- Complementary to BTA1576S3
- Pb-free lead plating and halogen-free package

## Symbol

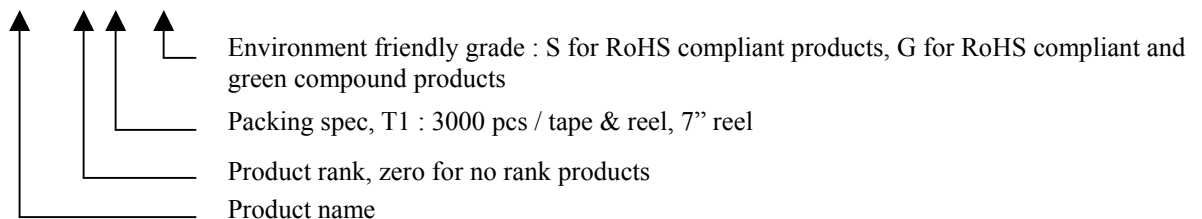


## Outline



## Ordering Information

Device	Package	Shipping
BTC4081S3-R-T1-G	SOT-323 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel





**Absolute Maximum Ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V <sub>CB0</sub>	100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	65	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Collector Current	I <sub>C</sub>	150	mA
Peak Collector Current	I <sub>CM</sub>	300	mA
Peak Base Current	I <sub>BM</sub>	100	mA
Power Dissipation	P <sub>D</sub>	225	mW
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	555	°C/W
Operating Junction and Storage Temperature range	T <sub>j</sub> ; T <sub>stg</sub>	-65~+150	°C

**Characteristics** (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CB0</sub>	100	-	-	V	I <sub>C</sub> =100μA
BV <sub>CEO</sub>	65	-	-	V	I <sub>C</sub> =1mA
BV <sub>EBO</sub>	7	-	-	V	I <sub>E</sub> =50μA
I <sub>CB0</sub>	-	-	30	nA	V <sub>CB</sub> =100V
I <sub>EBO</sub>	-	-	30	nA	V <sub>EB</sub> =7V
*V <sub>CE(sat)</sub>	-	47	80	mV	I <sub>C</sub> =110μA, I <sub>B</sub> =10μA
*V <sub>CE(sat)</sub>	-	58	95	mV	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA
*V <sub>CE(sat)</sub>	-	79	120	mV	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA
*V <sub>CE(sat)</sub>	-	123	180	mV	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA
*V <sub>CE(sat)</sub>	-	148	225	mV	I <sub>C</sub> =100mA, I <sub>B</sub> =5mA
*V <sub>BE(sat)</sub>	-	711	930	mV	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA
*V <sub>BE(sat)</sub>	-	867	980	mV	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA
*V <sub>BE(sat)</sub>	-	853	960	mV	I <sub>C</sub> =100mA, I <sub>B</sub> =5mA
*V <sub>BE(on)</sub>	600	646	700	mV	V <sub>CE</sub> =5V, I <sub>C</sub> =2mA
*V <sub>BE(on)</sub>	-	692	750	mV	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA
*h <sub>FE 1</sub>	160	-	-	-	V <sub>CE</sub> =5V, I <sub>C</sub> =10μA
*h <sub>FE 2</sub>	200	290	450	-	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA
f <sub>T</sub>	80	180	-	MHz	V <sub>CE</sub> =12V, I <sub>C</sub> =2mA, f=100MHz
C <sub>ob</sub>	-	2	3.5	pF	V <sub>CB</sub> =10V, f=1MHz
C <sub>ib</sub>	-	13.7	20	pF	V <sub>EB</sub> =0.5V, f=1MHz

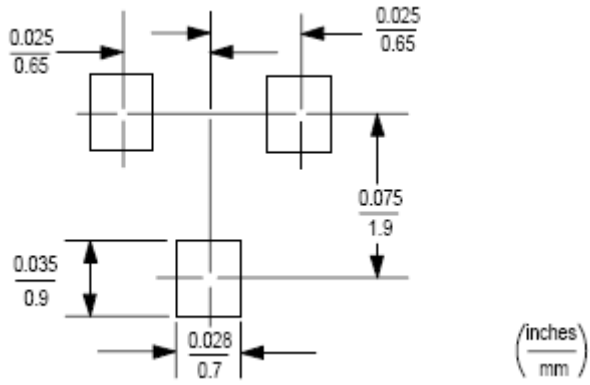
\*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

**Classification Of h<sub>FE 2</sub>**

Rank	R
Range	200~450

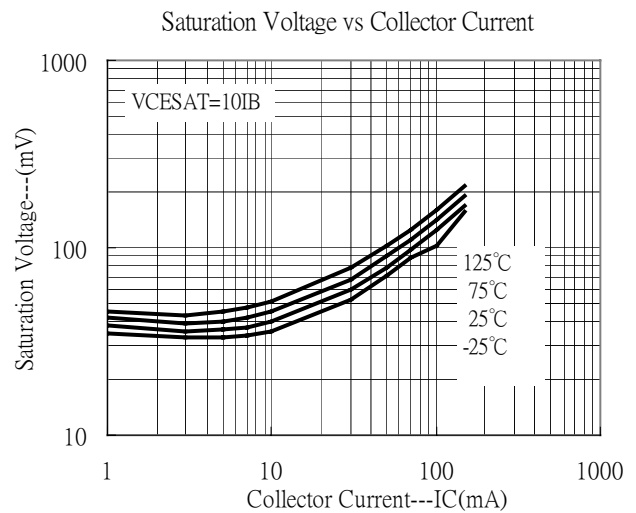
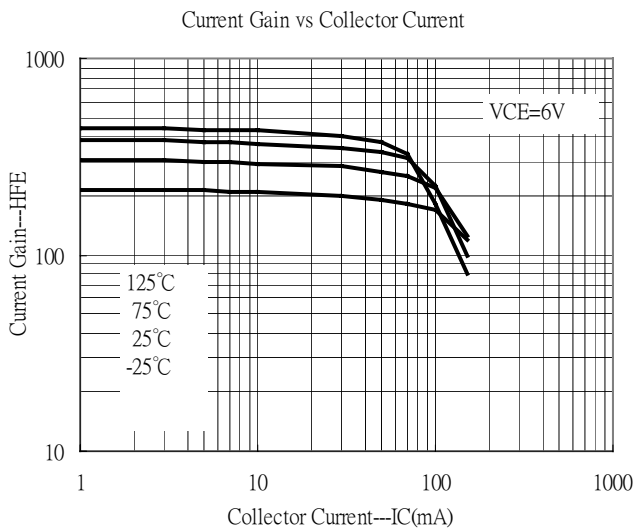
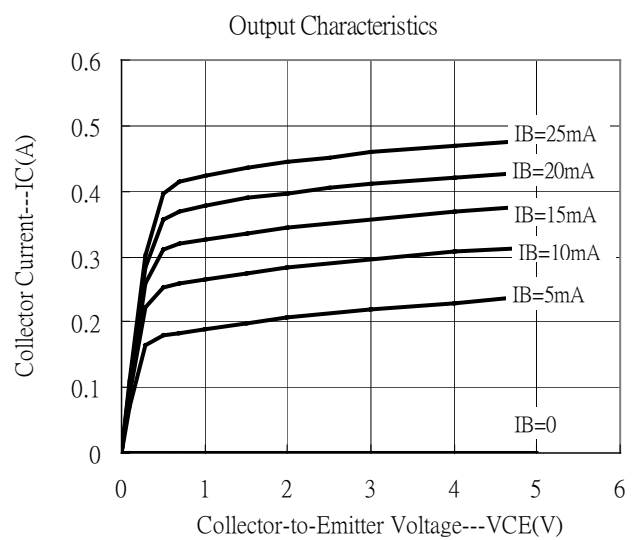
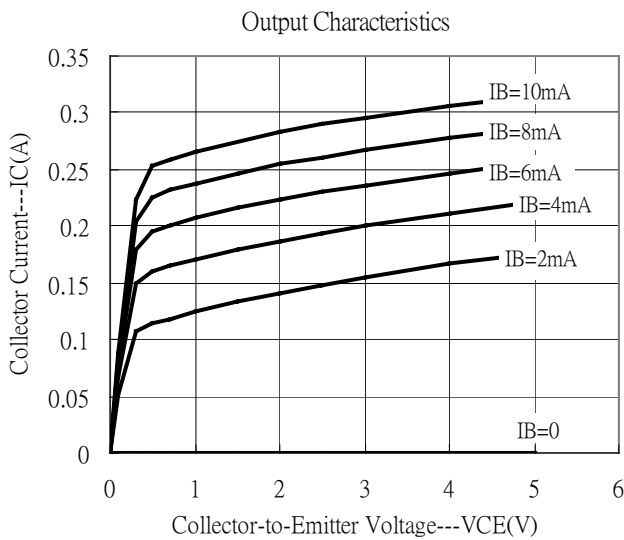
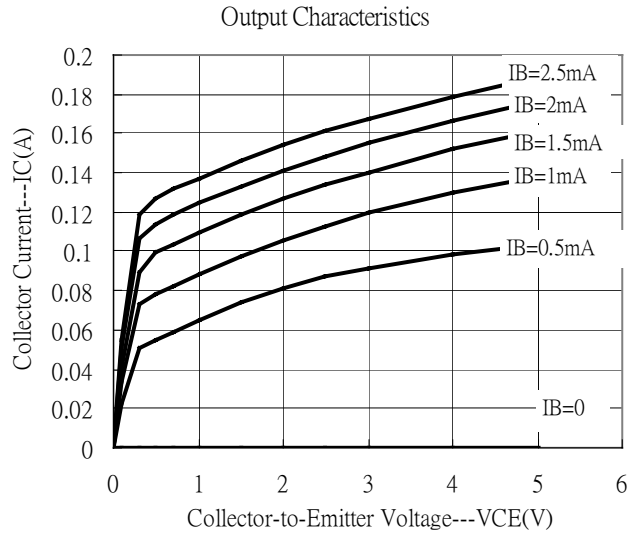
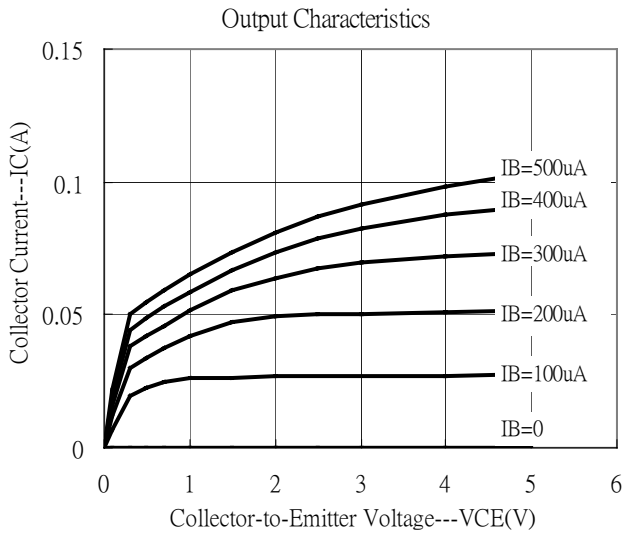


### Recommended Footprint



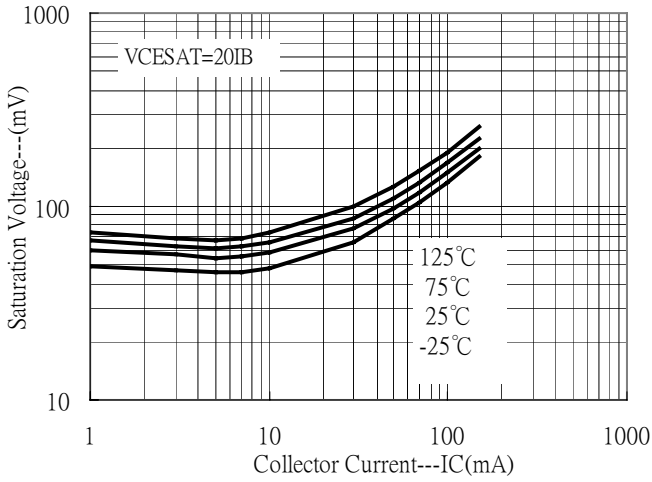


### Typical Characteristics

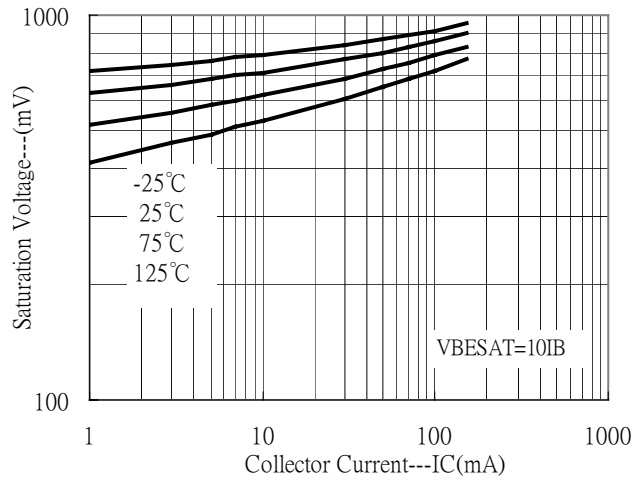


**Typical Characteristics(Cont.)**

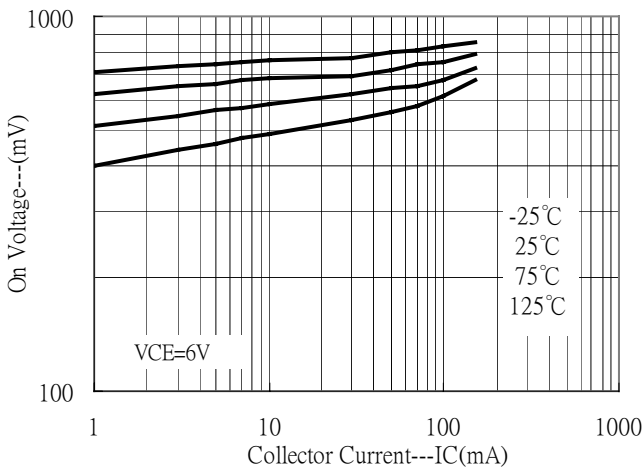
Saturation Voltage vs Collector Current



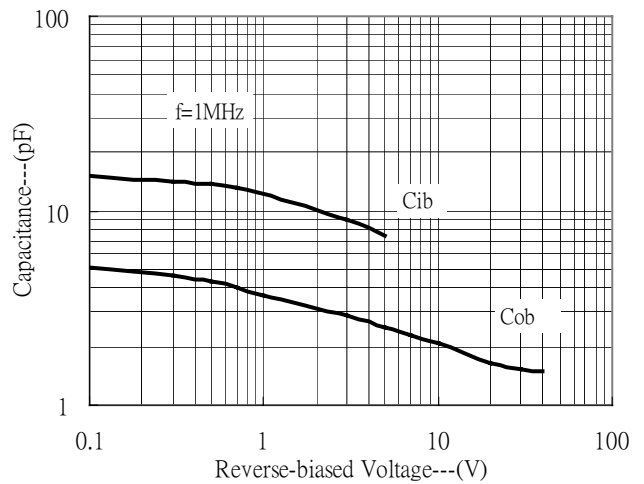
Saturation Voltage vs Collector Current



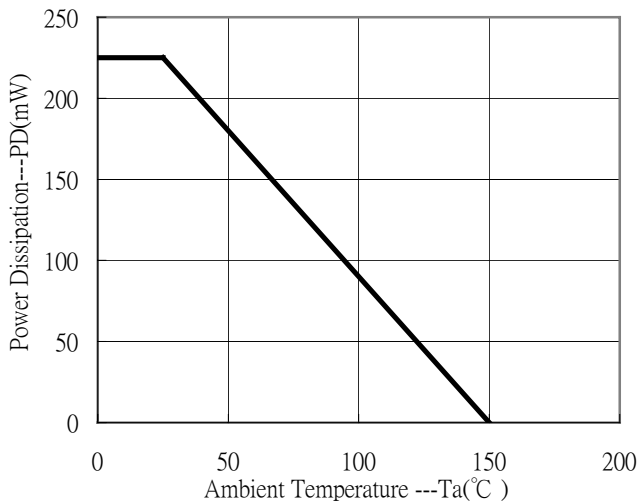
On Voltage vs Collector Current



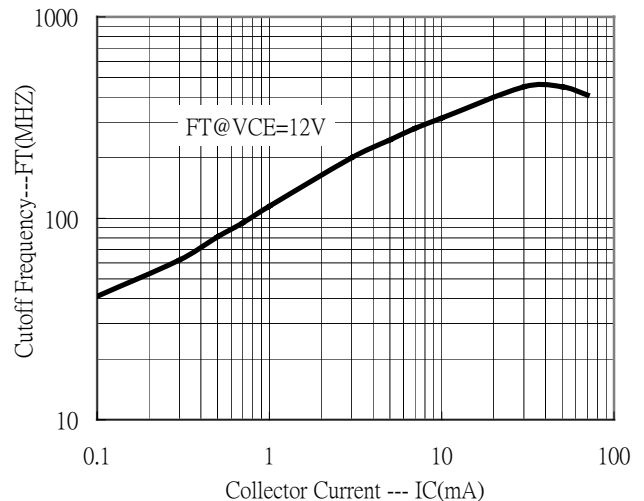
Capacitance Characteristics



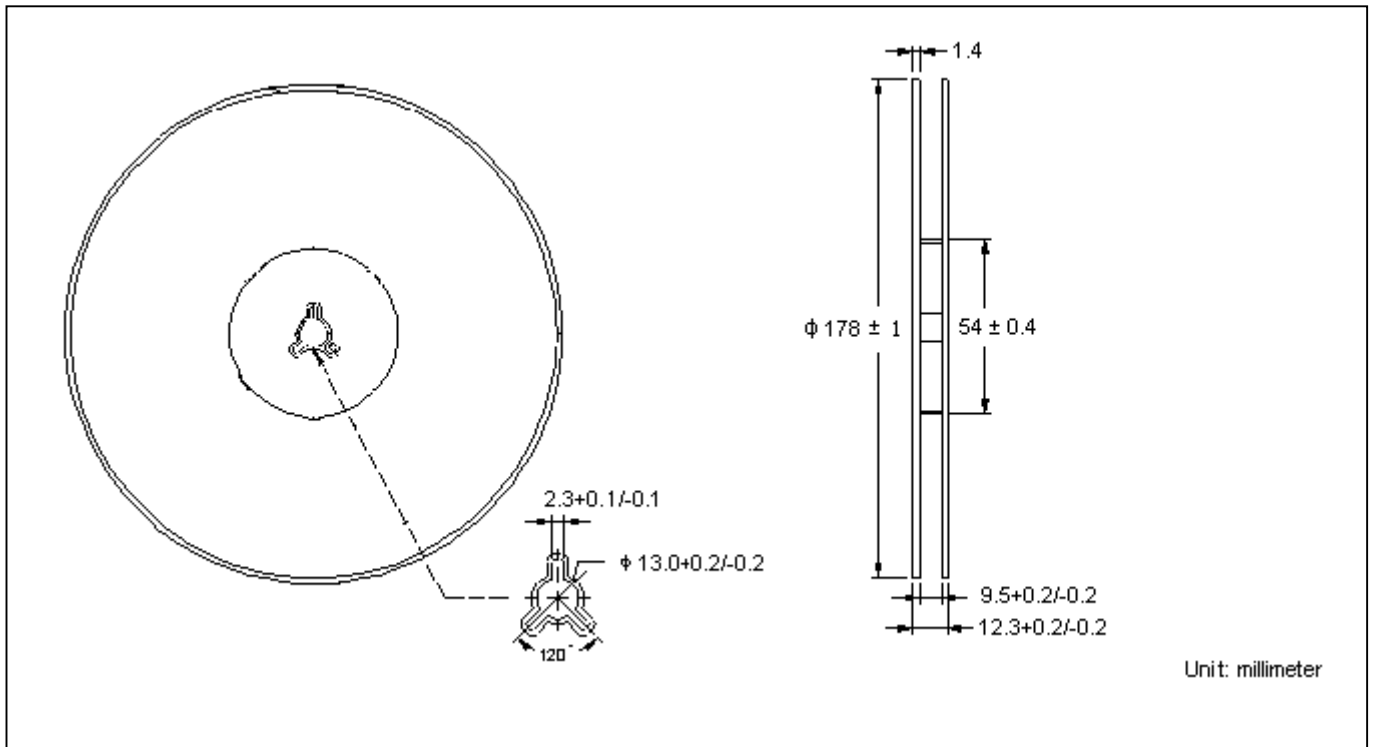
Power Derating Curve



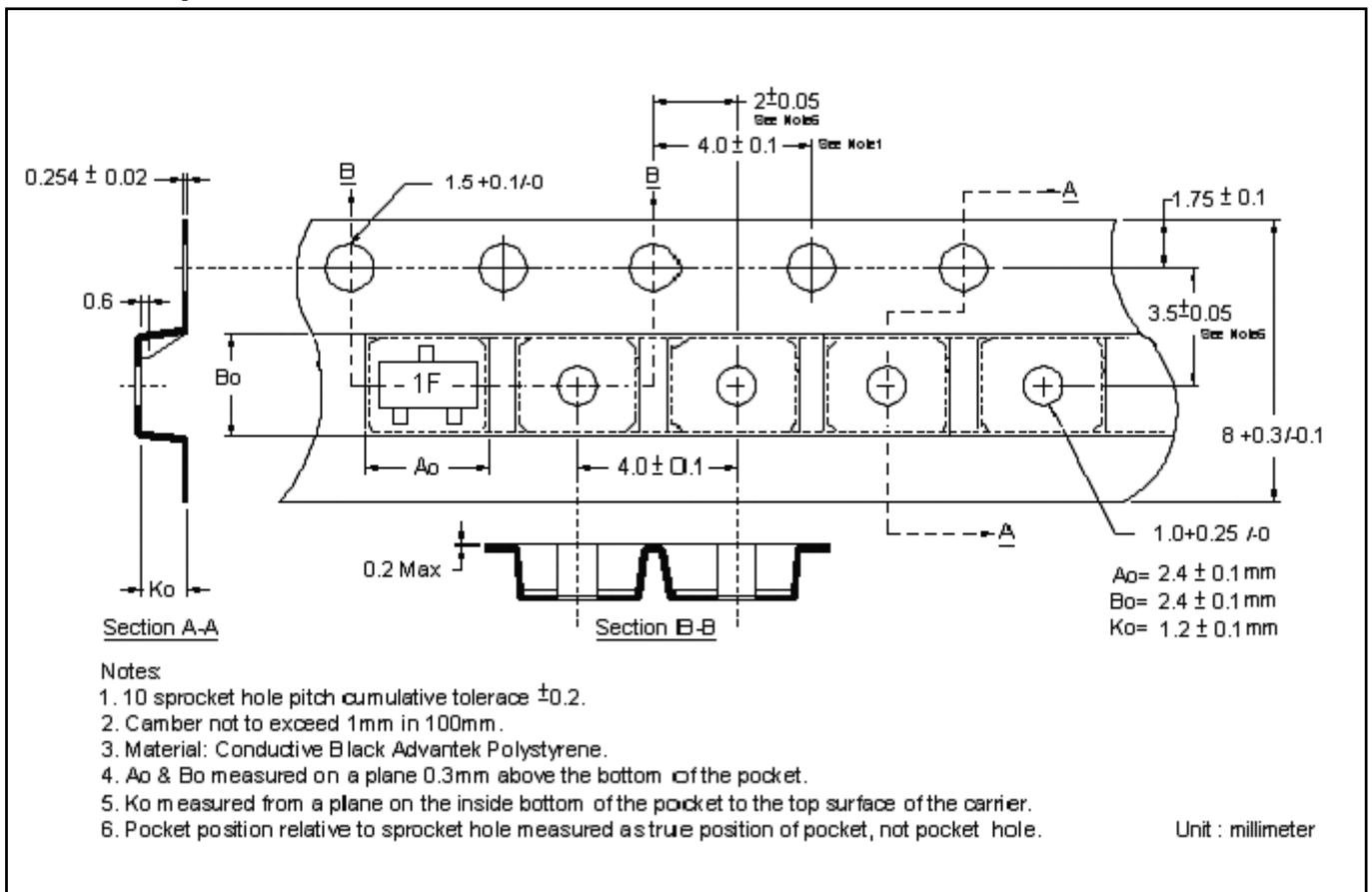
Cutoff Frequency vs Collector Current



**Reel Dimension**



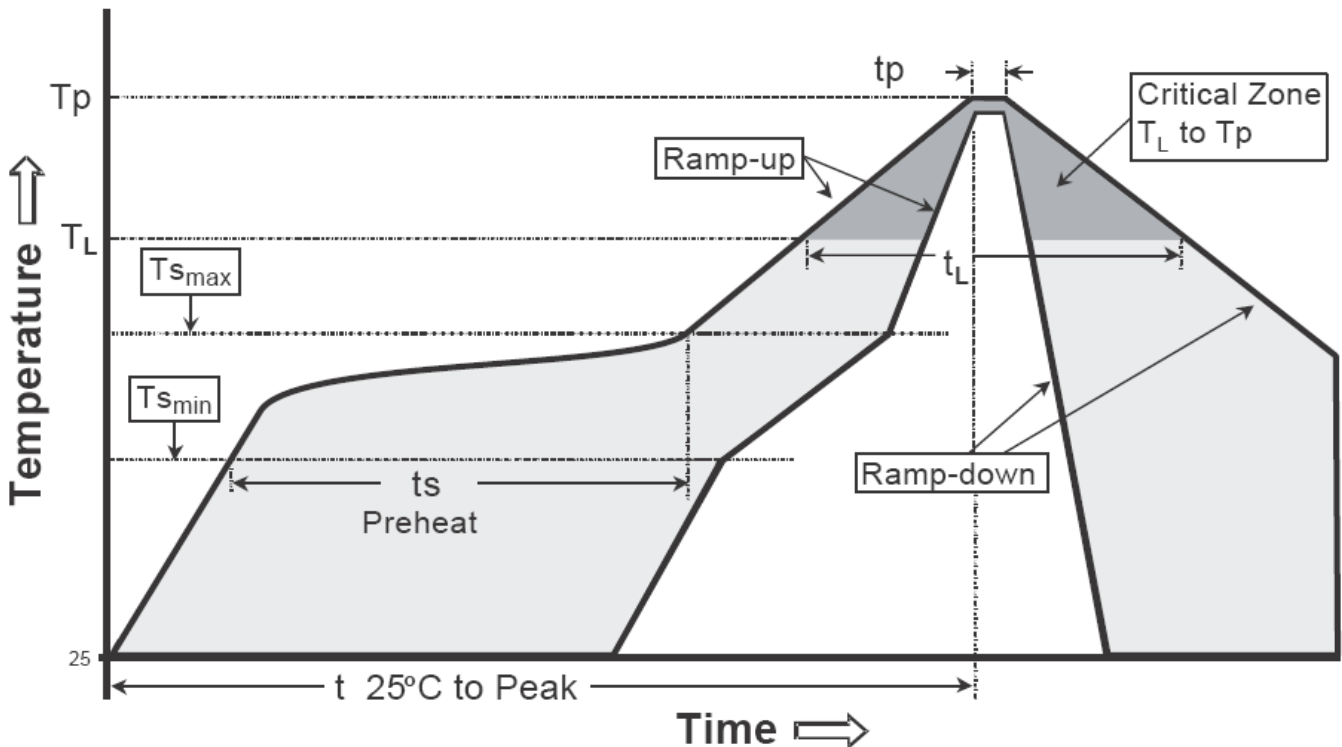
**Carrier Tape Dimension**



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

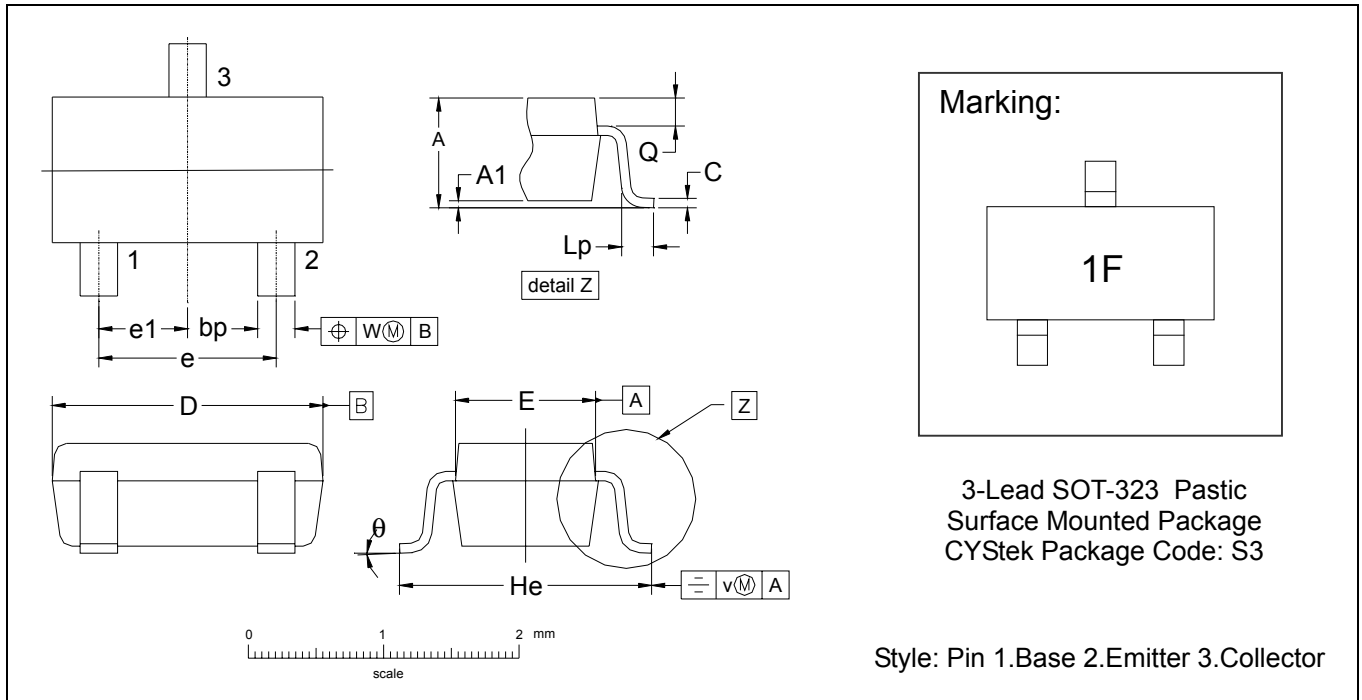
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> )	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T <sub>s min</sub> )	100°C	150°C
-Temperature Max(T <sub>s max</sub> )	150°C	200°C
-Time(t <sub>s min</sub> to t <sub>s max</sub> )	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak Temperature(T <sub>P</sub> )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(t <sub>p</sub> )	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOT-323 Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0315	0.0433	0.80	1.10	e1	0.0256*		0.65*	
A1	0.0000	0.0039	0.00	0.10	He	0.0846	0.0965	2.15	2.45
bp	0.0078	0.0157	0.20	0.40	Lp	0.0105	0.0181	0.26	0.46
C	0.0031	0.0059	0.08	0.15	Q	0.0051	0.0091	0.13	0.23
D	0.0709	0.0866	1.80	2.20	v	0.0079	-	0.2	-
E	0.0453	0.0531	1.15	1.35	w	0.0079	-	0.2	-
e	0.0472	0.0551	1.20	1.40	θ	0°	8°	0°	8°

Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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